

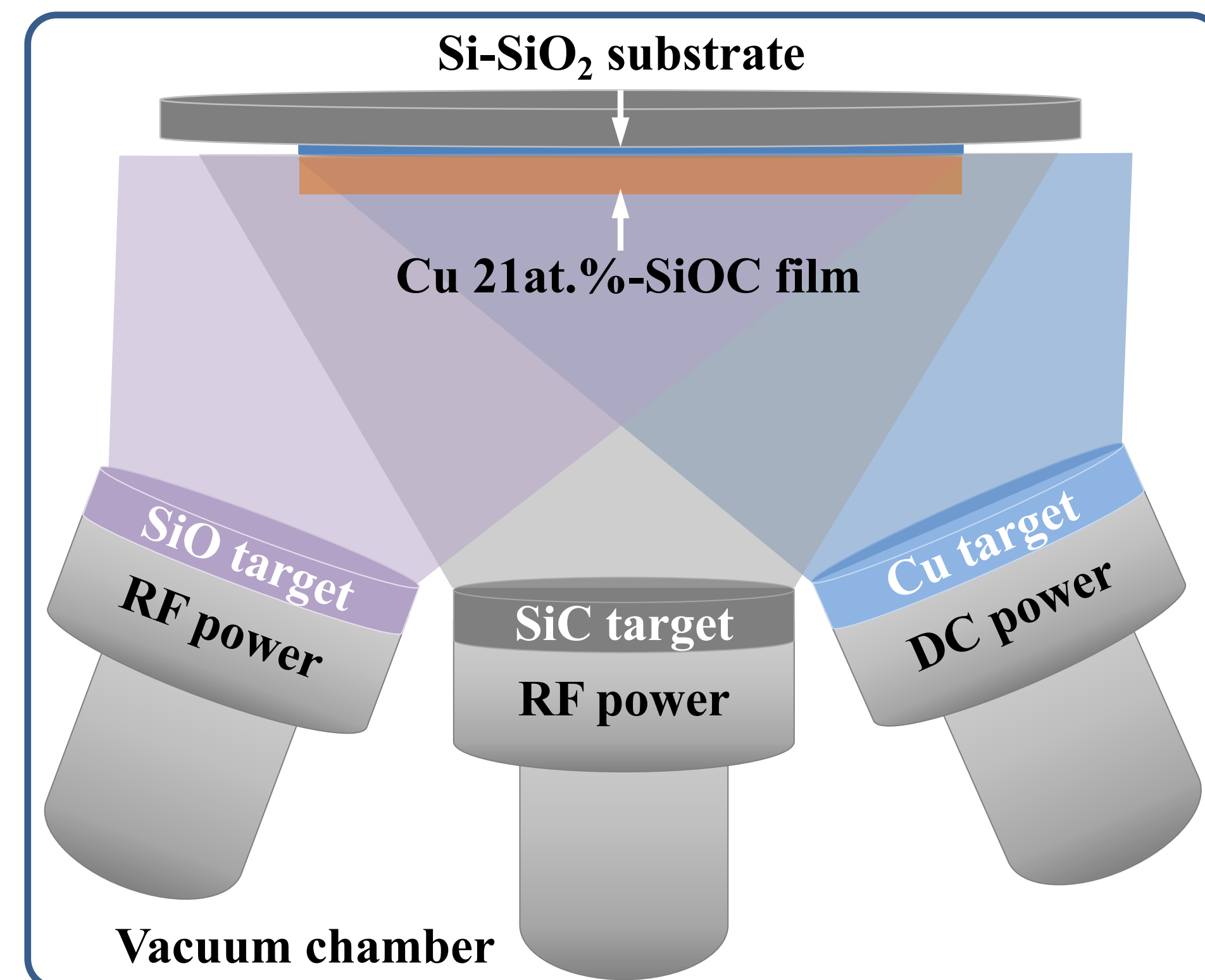
Ceramic nanowelding via in-situ growth of metal whiskers

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Ceramic nanowelding is extremely difficult to be achieved due to the high melting point, good insulation and low diffusivity of ceramic materials, and poor infiltration and large thermal expansion coefficients mismatch between ceramic and metal. Here, we demonstrated Metal-amorphous ceramic composites with high irradiation resistance can be used to glue ceramics and achieve high electric conductivity at extreme environments. Using Cu-SiOC composite film, we examined ceramic nanowelding through in-situ growth of Cu whiskers. The Cu whiskers can penetrate the whole film and joint the two films together, significantly increasing the conductivity of ceramic. This work was supported by NCESR and will be explored further for external funding.

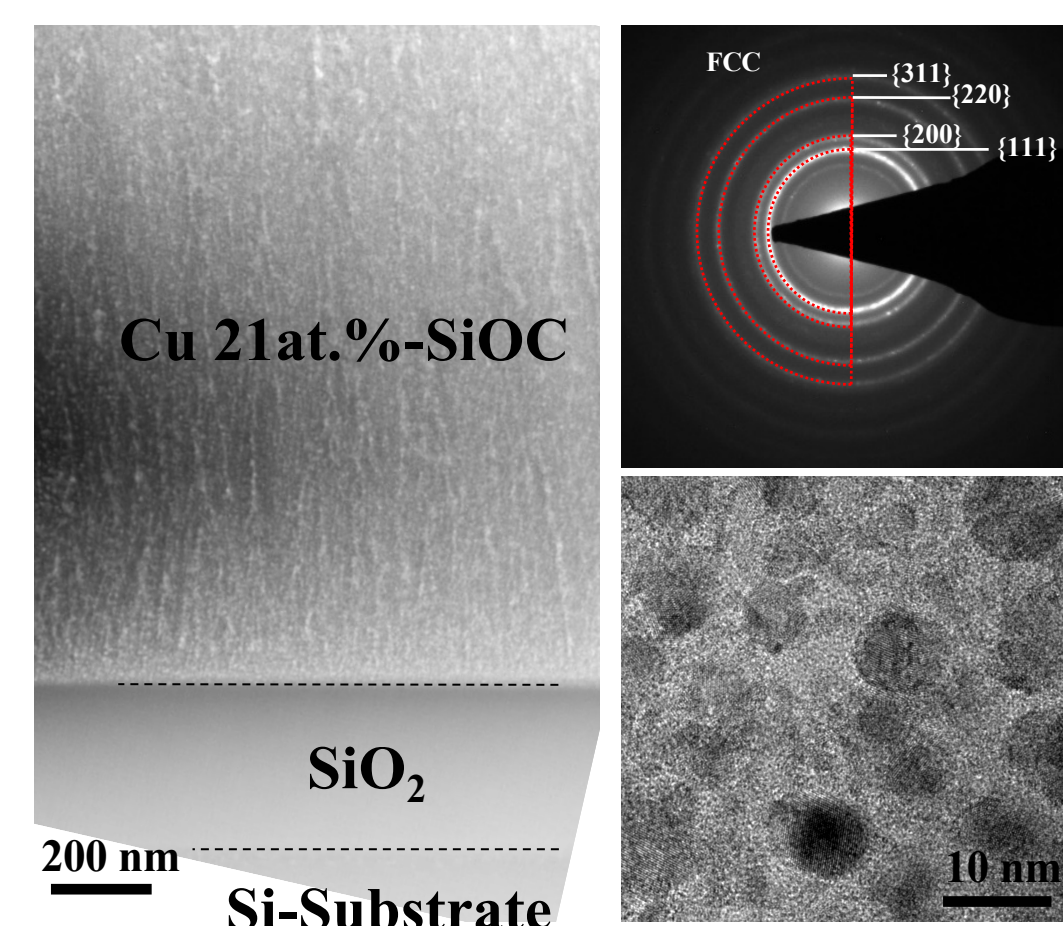
Cu-SiOC film fabrication

Co-sputtering Cu, SiO₂ and SiC targets by magnetron sputtering techniques at room temperature

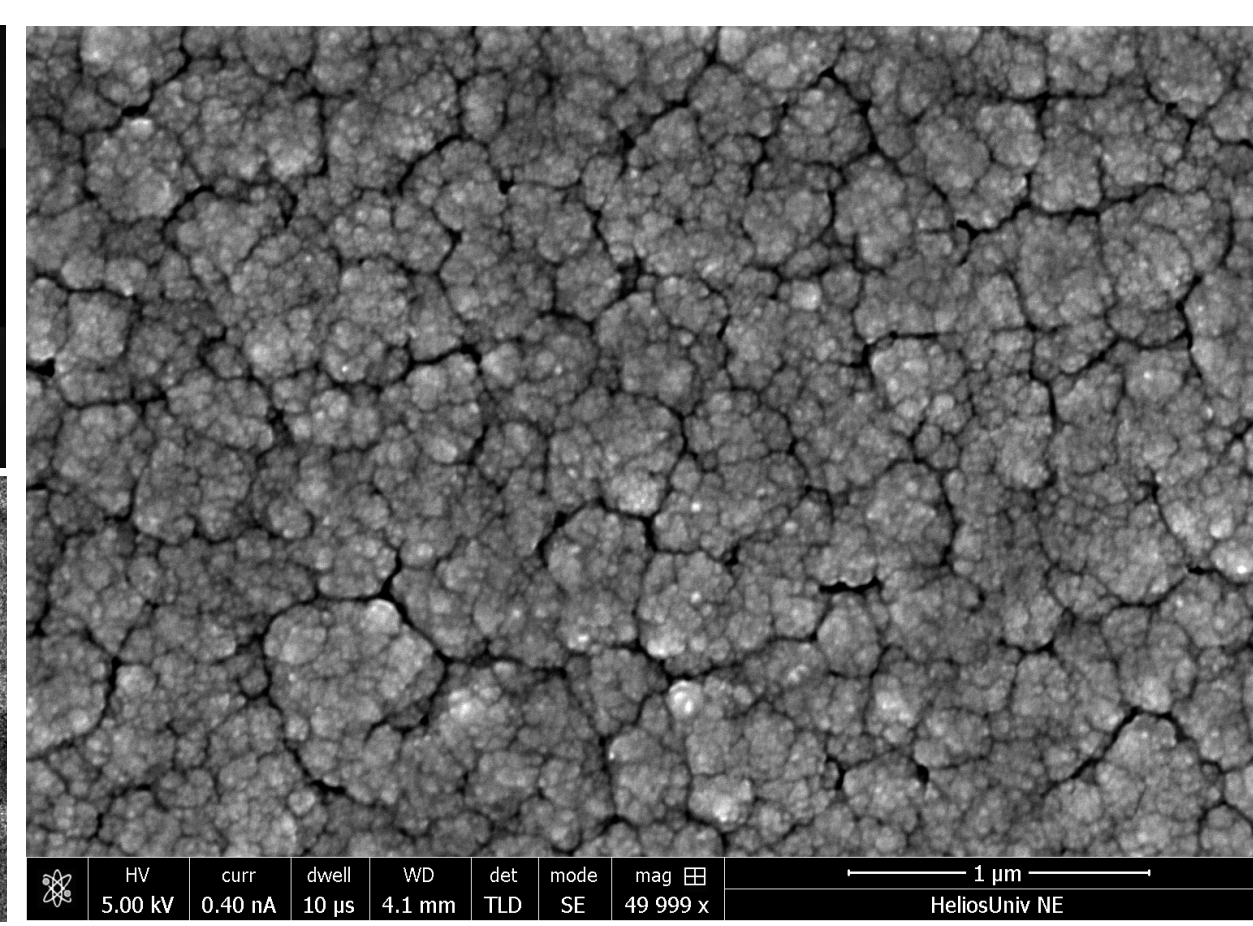


Microstructures in as-deposited state

TEM – cross-section view



SEM - plane view

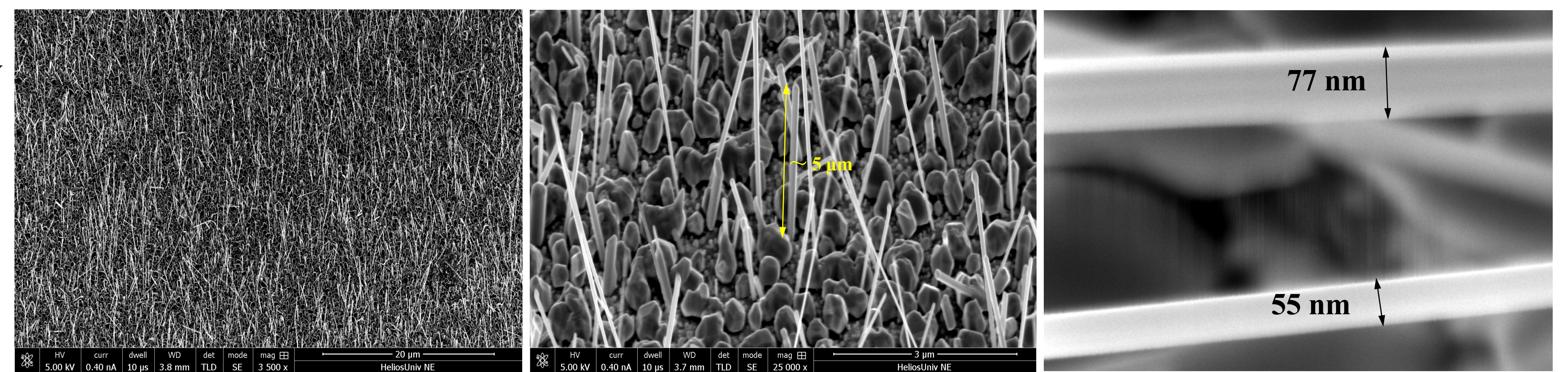


Columnar distribution of crystalline Cu nanoparticles along the growth direction of the film

Formation of Cu whiskers by annealing (≥ 300 °C)

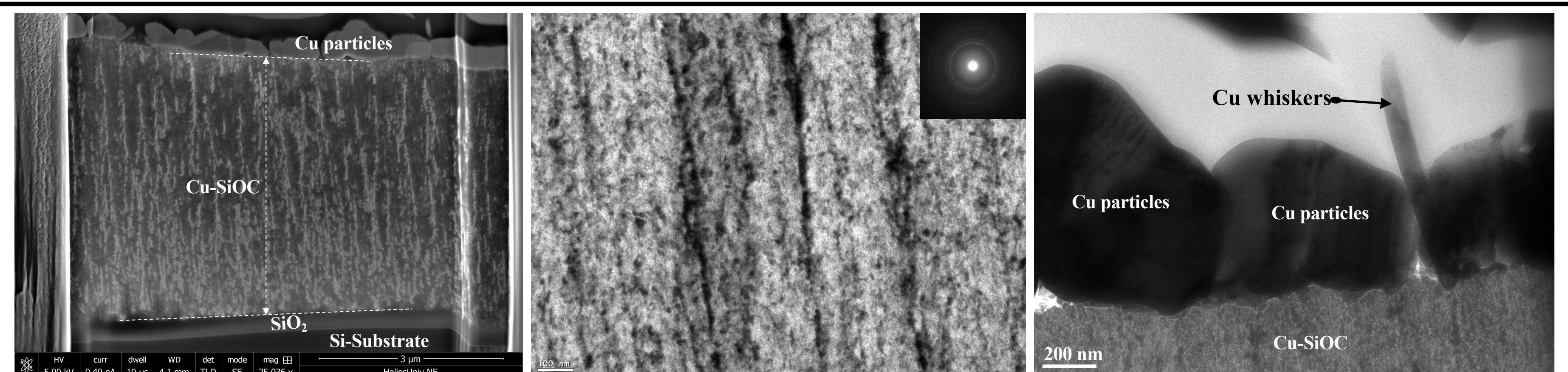
SEM - plane view

Cu whiskers:
diameter < 100 nm;
length ~ 5 μ m

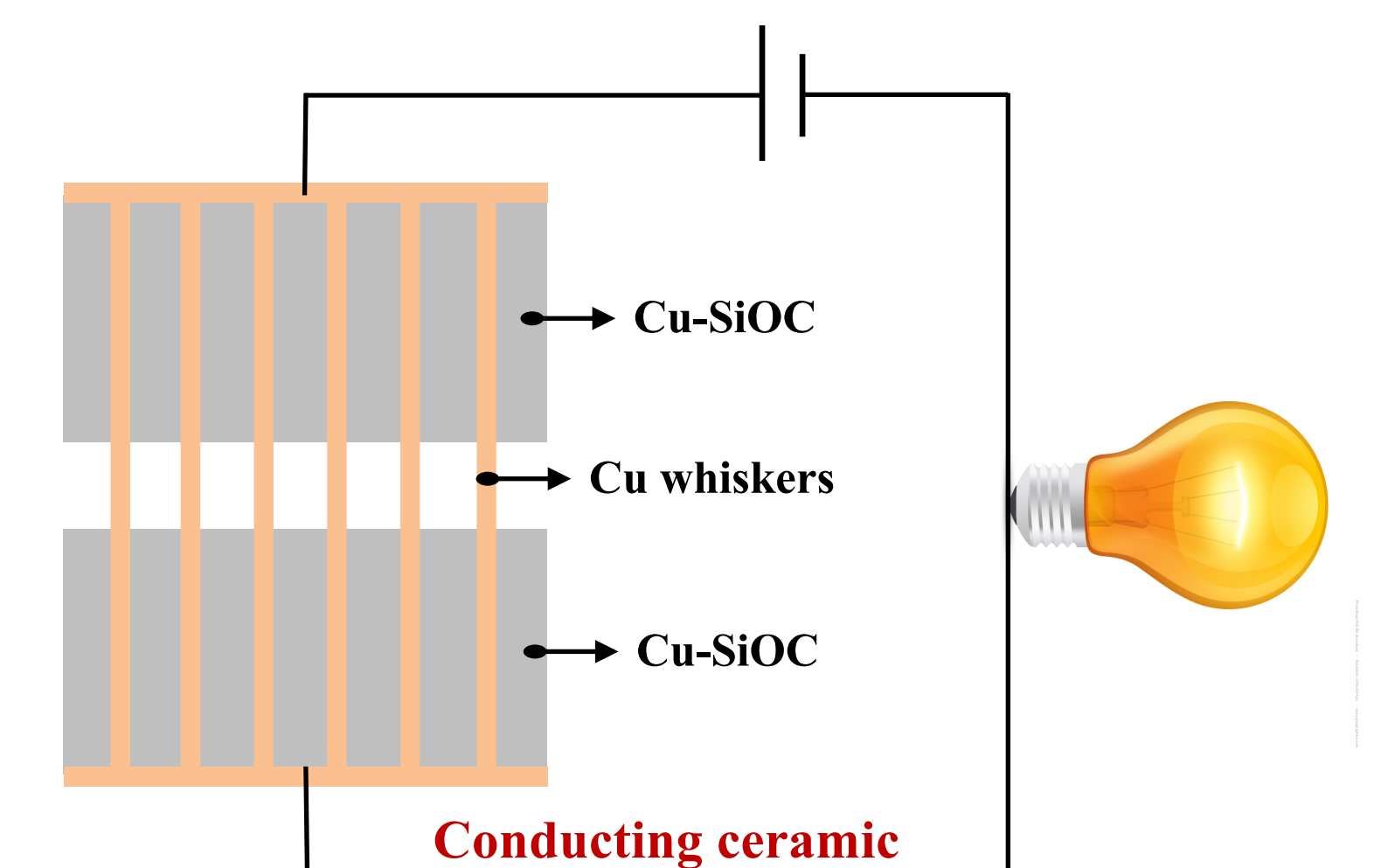
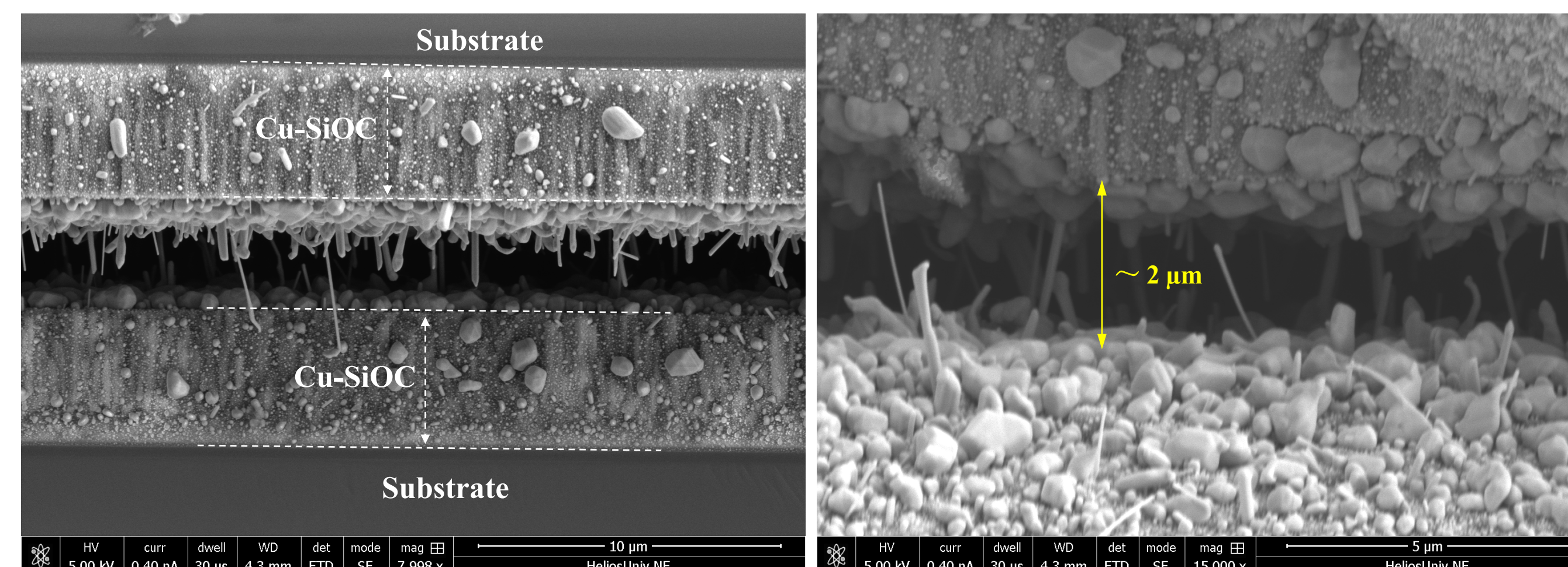


TEM/SEM
cross-section view

Cu whiskers penetrate
the whole film



Ceramic nanowelding via in-situ growth of metal whiskers



Cu atoms in the Cu-SiOC composite diffuse to the surface of the film after annealing at low temperatures (≥ 300 °C), leading to formation of numerous nano-sized Cu particles and whiskers. The Cu whiskers penetrate the whole film and joint the two films together, which can significantly increase the conductivity of ceramic. We provide a novel concept to achieve ceramic nanowelding, and design conducting ceramic materials via in-situ growth of metal whiskers.